

N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

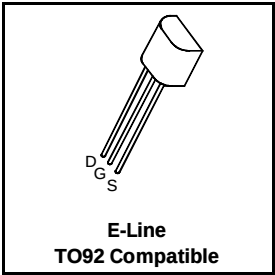
BS107P

ISSUE 2 – SEPT 93

FEATURES

- * 200 Volt V_{DS}
- * $R_{DS(on)}=23\Omega$

REFER TO BS107PT FOR GRAPHS



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	200	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	0.12	A
Pulsed Drain Current	I_{DM}	2	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	200	230		V	$I_D=100\mu A, V_{GS}=0V$
Gate Body Leakage	I_{GSS}			10	nA	$V_{GS}=15V, V_{DS}=0V$
Drain Cut-Off Current	I_{DSS}			30	nA	$V_{GS}=0V, V_{DS}=130V$
Drain Cut-Off Current	I_{DSX}			1	μA	$V_{GS}=0.2V, V_{DS}=70V$
Static Drain-Source on-State Resistance	$R_{DS(on)}$		15	23 30	Ω Ω	$V_{GS}=2.6V, I_D=25mA^*$ $V_{GS}=5V, I_D=100mA^*$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$